

SDB310WS

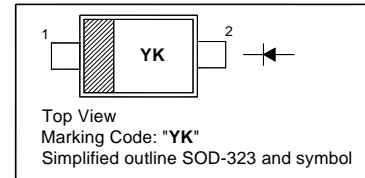
SCHOTTKY BARRIER DIODE

Features

- Low power rectified
- Silicon epitaxial type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

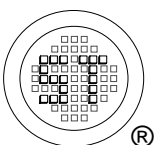


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I_F	0.2	A
Repetitive Peak Forward Current	I_{FRM}	0.5	A
Non-Repetitive Peak Forward Current (8.3 ms)	I_{FSM}	1	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 30\text{ mA}$	V_F	0.4 0.5	V
Reverse Current at $V_R = 30\text{ V}$	I_R	1	μA
Total Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	10	pF



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Fig. 1 I_F - V_F

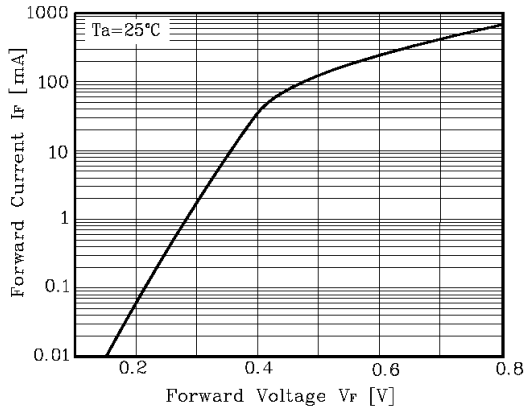


Fig. 2 I_R - V_R

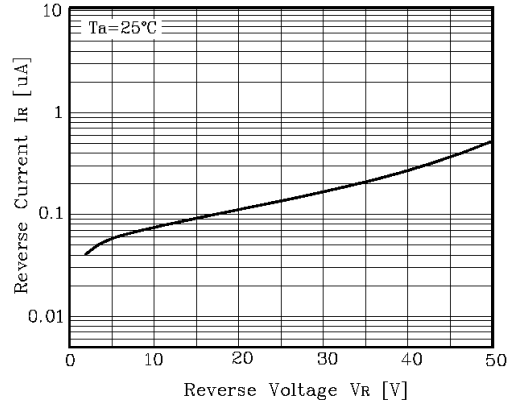
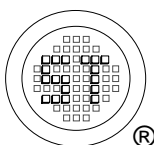
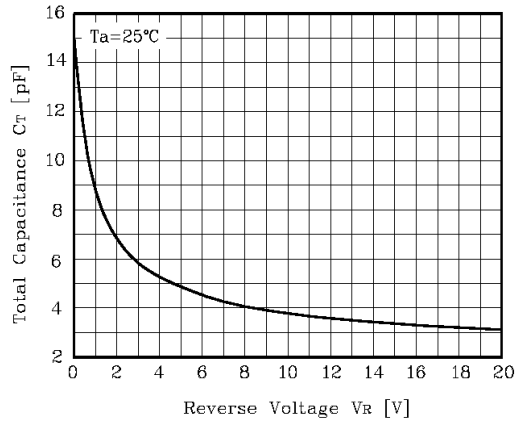


Fig. 3 C_T - V_R



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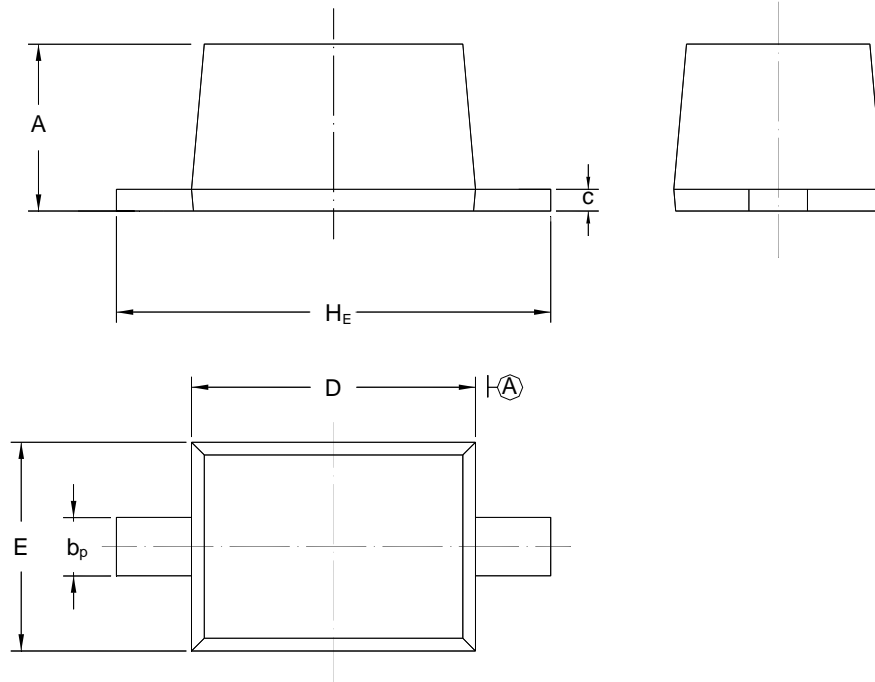
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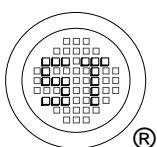
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



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